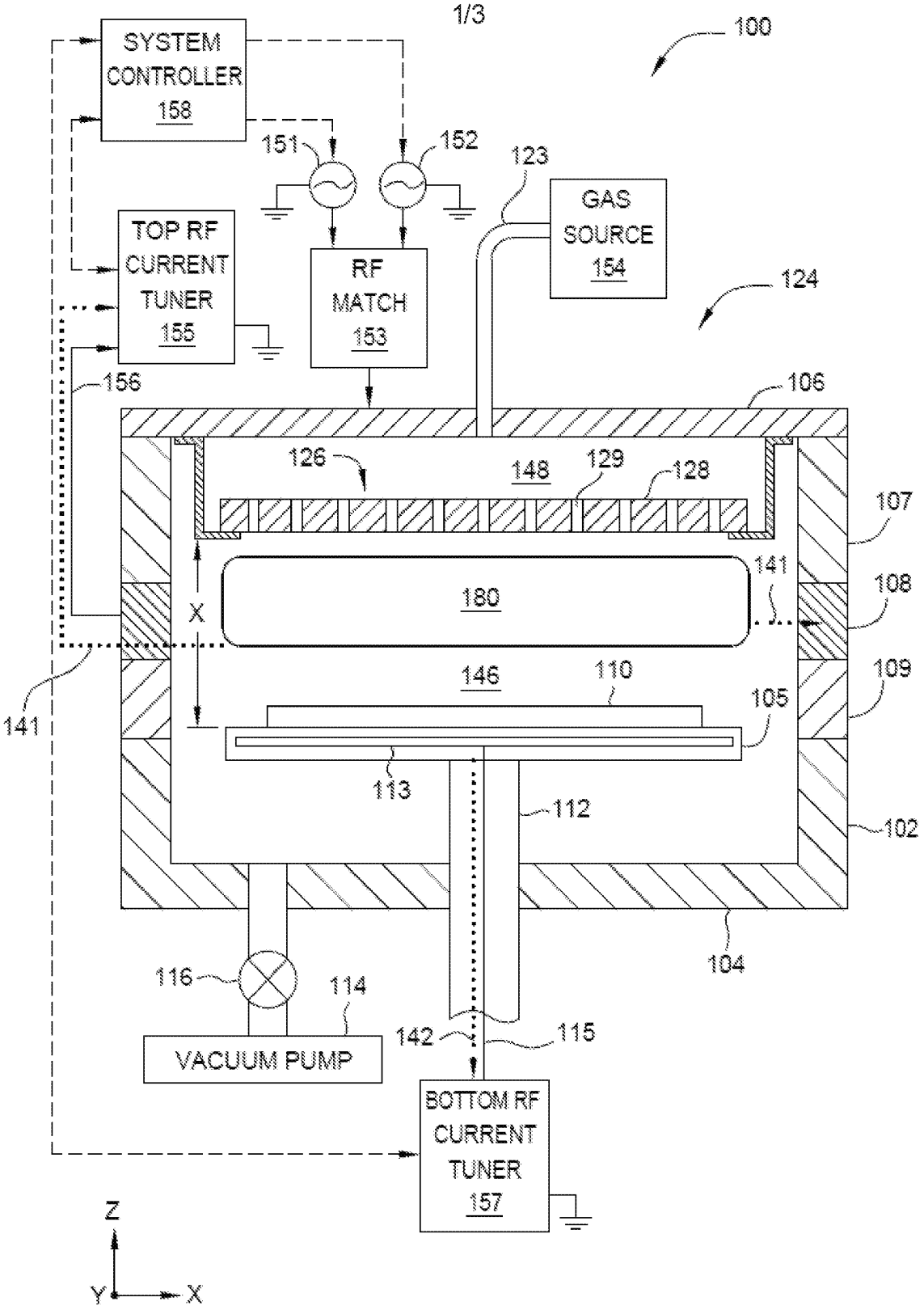

SYSTEM CONTROLLER 158
100
151
152
123
GAS SOURCE 154
TOP RF CURRENT TUNER 155
RF MATCH 153
124
156
106
126
148
129
128
107
141
180
108
X
146
110
109
105
141
113
112
102
104
116
114
VACUUM PUMP
142
115
BOTTOM RF CURRENT TUNER 157
Z
Y
X

FIG. 1

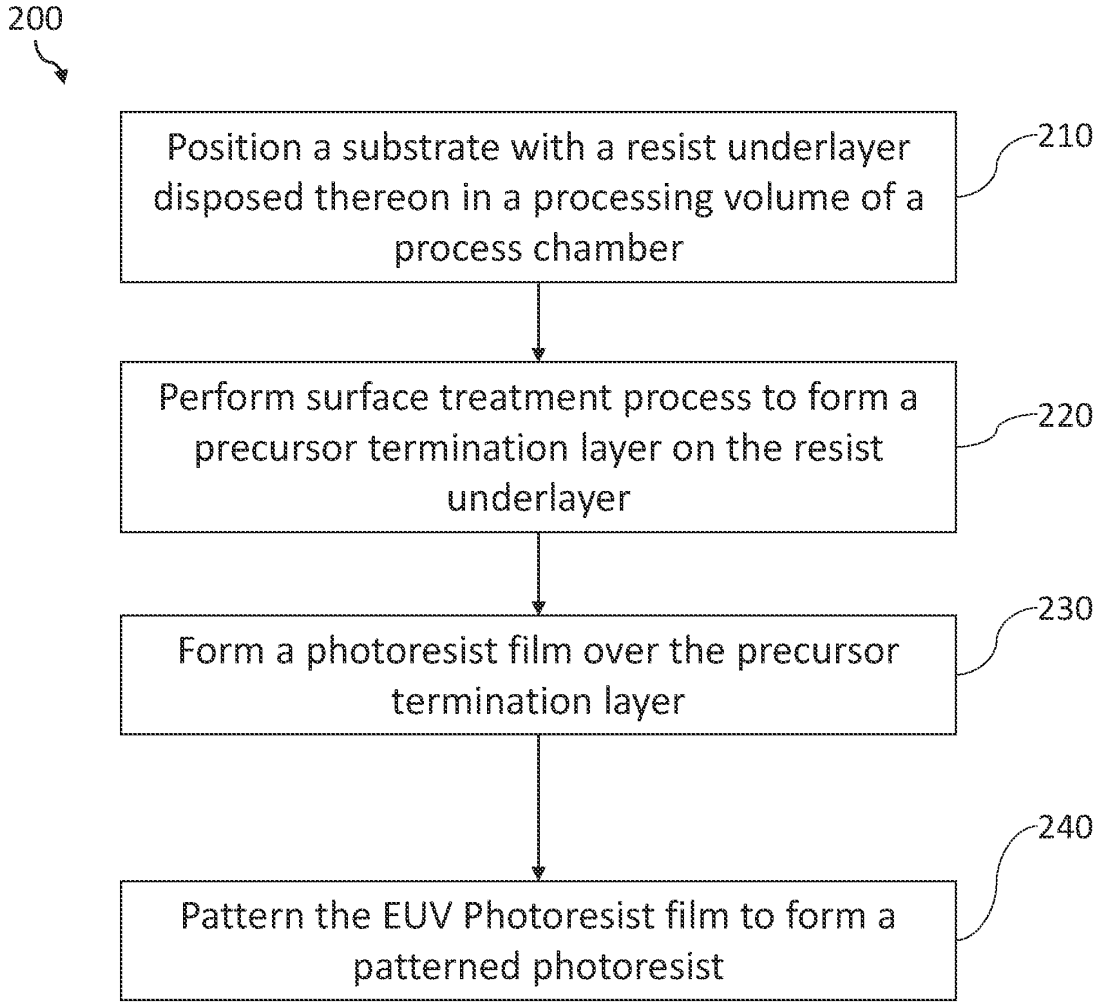

200
Position a substrate with a resist underlayer disposed thereon in a processing volume of a process chamber
210
Perform surface treatment process to form a precursor termination layer on the resist underlayer
220
Form a photoresist film over the precursor termination layer
230
Pattern the EUV Photoresist film to form a patterned photoresist
240

FIG. 2

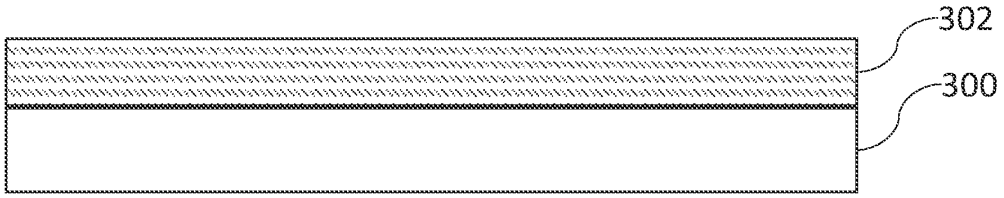


FIG. 3A

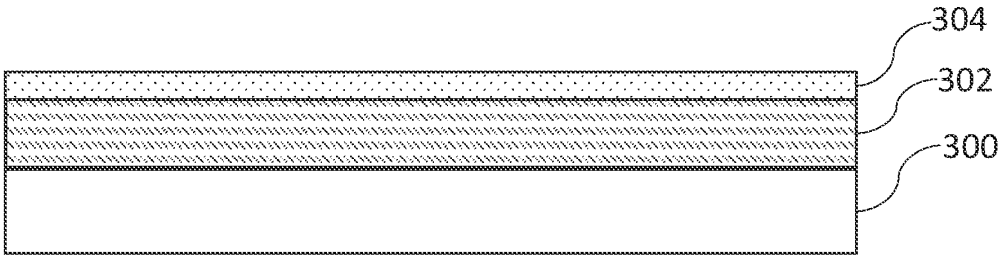


FIG. 3B

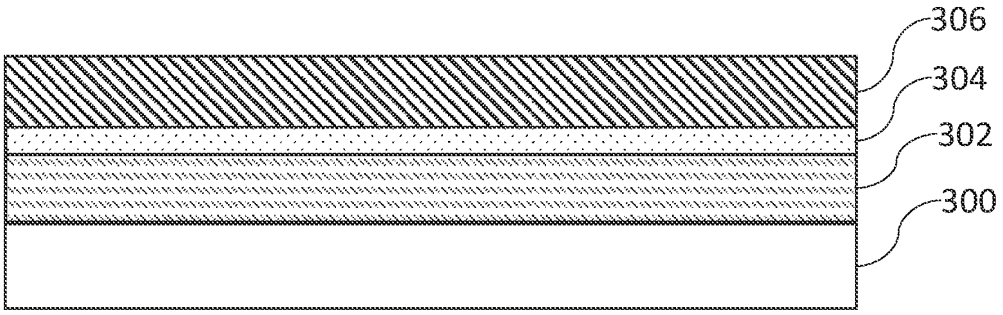


FIG. 3C

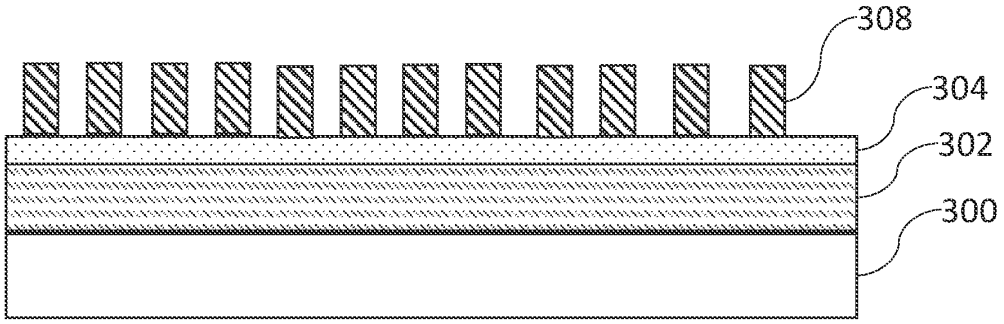


FIG. 3D